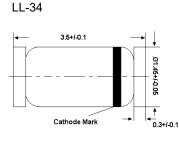
LL4150APF

Silicon Epitaxial Planar Switching Diode

Features

- Lead Free
- Fast switching speed
- High reliability
- High conductance
- For general purpose switching applications



Glass case MiniMELF Dimensions in mm

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V _{RM}	50	V
Average Rectified Forward Current	IF(AV)	300	mA
Forward Continuous Current	IFM	400	mA
Power Dissipation	P _{tot}	500	mW
Junction Temperature	Tj	175	٥C
Storage Temperature Range	T _{stg}	- 65 to +175	٥C

Thermal Characteristics

Thermal Resistance Junction to Ambient Air ¹⁾	300	°C/W

¹⁾ Valid provided that electrodes are kept at ambient temperature.

Characteristics at Ta = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 300 mA	VF	1.2	V
Peak Reverse Current at $V_R = 50 \text{ V}$	IR	100	nA
Reverse Recovery Time at I_F = 10 mA , I_{rr} = 0.1 x I_R , V_R = 6 V, R_L = 100 Ω	trr	4	ns

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